



JNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Seiji SARAYAMA et al.

Serial No.: 10/601,301

Group Art Unit: 2818

Date Filed: June 13, 2003

Examiner: Tu-Tu Ho

For:

Reg. No. 40,837

PRODUCTION OF A GaN BULK CRYSTAL SUBSTRATE SEMICONDUCTOR DEVICE FORMED ON A GaN BULK CRYSTAL SUBSTRATE

I hereby certify that this correspondence is being deposited this date with the U.S. Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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## INFORMATION DISCLOSURE STATEMENT

Pursuant to the applicant's duty of disclosure, the information listed in the attached Form PTO-1449 is brought to the attention of the Examiner. A copy of the information listed in the attached Form PTO-1449 is submitted herewith.

The references listed on the annexed Form PTO-1449 were cited in a February 28, 2006 official action in connection with a corresponding Japanese application. A copy of the February 28, 2006 Japanese official action is enclosed.

It is respectfully requested that the information cited in the annexed Form PTO-1449 be considered by the Examiner in connection with the above-identified patent application, and that such art be made of record in said application.

The citation of the listed items is not a representation that they constitute a complete or exhaustive listing of the relevant art or that these items are prior art. The items listed are submitted in good faith, but are not intended to substitute for the Examiner's search. It is hoped, 4.1

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Dkt. 2271/62289-Z

however, that in addition to apprising the Examiner of the particular items, they will assist in

identifying fields of search and in making as full and complete a search as possible.

The filing of this Information Disclosure Statement is not an admission that the

information cited herein is, or is considered to be, material to patentability as defined in 37

C.F.R. §1.56(b).

This Information Disclosure Statement is being filed pursuant to 37 C.F.R. §1.97(c)(1),

after the mailing date of a first Office Action, but before the close of prosecution in the

application.

Applicant certifies, pursuant to 37 C.F.R. §1.97(e)(1), that each item of information

contained in this Information Disclosure Statement was first cited in any communication from a

foreign patent office in a counterpart foreign application not more than three months prior to the

filing of this Information Disclosure Statement. The date of mailing of the Japanese Office

Action is February 28, 2006, and therefore this Information Disclosure Statement is being timely

filed, pursuant to 37 C.F.R. §1.97(c)(1).

The Patent Office is hereby authorized to charge any fees that are required for

consideration of this Information Disclosure Statement and to credit any overpayment to our

Deposit Account No. 03-3125.

Respectfully submitted,

Paul Teng, Reg. No. 40,8

Attorney for Applicants

Cooper & Dunham LLP

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Form PTO-1449  Patent and Trademark Office  INFORMATION DISCLOSURE CITATION  (Use several sheets if necessary)												Atty. Dock 2271/622		Serial No. 10/601,301		
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